# E · / Hat lice Semiconductor Corporation - <u>LCMXO3L-9400E-6MG256I Datasheet</u>



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#### Understanding <u>Embedded - FPGAs (Field</u> <u>Programmable Gate Array)</u>

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

#### **Applications of Embedded - FPGAs**

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

#### Details

Product Status	Active
Number of LABs/CLBs	1175
Number of Logic Elements/Cells	9400
Total RAM Bits	442368
Number of I/O	206
Number of Gates	-
Voltage - Supply	1.14V ~ 1.26V
Mounting Type	Surface Mount
Operating Temperature	-40°C ~ 100°C (TJ)
Package / Case	256-VFBGA
Supplier Device Package	256-CSFBGA (9x9)
Purchase URL	https://www.e-xfl.com/product-detail/lattice-semiconductor/lcmxo3l-9400e-6mg256i

Email: info@E-XFL.COM

Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong



#### Table 1-1. MachXO3L/LF Family Selection Guide

Features		MachXO3L-640/ MachXO3LF-640	MachXO3L-1300/ MachXO3LF-1300	MachXO3L-2100/ MachXO3LF-2100	MachXO3L-4300/ MachXO3LF-4300	MachXO3L-6900/ MachXO3LF-6900	MachXO3L-9400/ MachXO3LF-9400
LUTs		640	1300	2100	4300	6900	9400
Distributed RAM (kbits)		5	10	16	34	54	73
EBR SRAM (	kbits)	64	64	74	92	240	432
Number of PL	Ls	1	1	1	2	2	2
Hardened	I <sup>2</sup> C	2	2	2	2	2	2
LUTs Distributed RAM EBR SRAM (kbi Number of PLLs Hardened Functions: MIPI D-PHY Su Multi Time Prog NVCM Programmable I Packages 36-ball WLCSP (3.2 mm x 2.5 m 49-ball WLCSP (3.2 mm x 3.2 m 81-ball WLCSP (3.8 mm x 3.8 m 121-ball csfBGA (6 mm x 6 mm, 256-ball csfBGA (9 mm x 9 mm, 324-ball csfBGA (10 mm x 10 mr 256-ball caBGA (14 mm x 14 mr 324-ball caBGA (15 mm x 15 mr	SPI	1	1	1	1	1	1
	Timer/Counter	1	1	1	1	1	1
	Oscillator	1	1	1	1	1	1
MIPI D-PHY Support Multi Time Programmable		Yes	Yes	Yes	Yes	Yes	Yes
	ogrammable	MachXO3L-640	MachXO3L-1300	MachXO3L-2100	MachXO3L-4300	MachXO3L-6900	MachXO3L-9400
Programmabl	le Flash	MachXO3LF-640	MachXO3LF-1300	MachXO3LF-2100	MachXO3LF-4300	MachXO3LF-6900	MachXO3LF-9400
Packages				ю			
			28				
				38			
					63		
		100	100	100	100		
		2	206	206	206	206	206
				268	268	281	
256-ball caBGA <sup>2</sup> (14 mm x 14 mm, 0.8 mm)			206	206	206	206	206
				279	279	279	
400-ball caB0 (17 mm x 17					335	335	335
484-ball caB0 (19 mm x 19							384

1. Package is only available for E=1.2 V devices.

2. Package is only available for C=2.5 V/3.3 V devices.

## Introduction

MachXO3<sup>™</sup> device family is an Ultra-Low Density family that supports the most advanced programmable bridging and IO expansion. It has the breakthrough IO density and the lowest cost per IO. The device IO features have the integrated support for latest industry standard IO.

The MachXO3L/LF family of low power, instant-on, non-volatile PLDs has five devices with densities ranging from 640 to 9400 Look-Up Tables (LUTs). In addition to LUT-based, low-cost programmable logic these devices feature Embedded Block RAM (EBR), Distributed RAM, Phase Locked Loops (PLLs), pre-engineered source synchronous I/O support, advanced configuration support including dual-boot capability and hardened versions of commonly used functions such as SPI controller, I<sup>2</sup>C controller and timer/counter. MachXO3LF devices also support User Flash Memory (UFM). These features allow these devices to be used in low cost, high volume consumer and system applications.

The MachXO3L/LF devices are designed on a 65nm non-volatile low power process. The device architecture has several features such as programmable low swing differential I/Os and the ability to turn off I/O banks, on-chip PLLs







 MachXO3L/LF-1300, MachXO3L/LF-2100, MachXO3L/LF-6900 and MachXO3L/LF-9400 are similar to MachXO3L/LF-4300. MachXO3L/LF-1300 has a lower LUT count, one PLL, and seven EBR blocks. MachXO3L/LF-2100 has a lower LUT count, one PLL, and eight EBR blocks. MachXO3L/LF-6900 has a higher LUT count, two PLLs, and 26 EBR blocks. MachXO3L/LF-9400 has a higher LUT count, two PLLs, and 48 EBR blocks.

• MachXO3L devices have NVCM, MachXO3LF devices have Flash.

The logic blocks, Programmable Functional Unit (PFU) and sysMEM EBR blocks, are arranged in a two-dimensional grid with rows and columns. Each row has either the logic blocks or the EBR blocks. The PIO cells are located at the periphery of the device, arranged in banks. The PFU contains the building blocks for logic, arithmetic, RAM, ROM, and register functions. The PIOs utilize a flexible I/O buffer referred to as a sysIO buffer that supports operation with a variety of interface standards. The blocks are connected with many vertical and horizontal routing channel resources. The place and route software tool automatically allocates these routing resources.

In the MachXO3L/LF family, the number of sysIO banks varies by device. There are different types of I/O buffers on the different banks. Refer to the details in later sections of this document. The sysMEM EBRs are large, dedicated fast memory blocks. These blocks can be configured as RAM, ROM or FIFO. FIFO support includes dedicated FIFO pointer and flag "hard" control logic to minimize LUT usage.

The MachXO3L/LF registers in PFU and sysI/O can be configured to be SET or RESET. After power up and device is configured, the device enters into user mode with these registers SET/RESET according to the configuration setting, allowing device entering to a known state for predictable system function.

The MachXO3L/LF architecture also provides up to two sysCLOCK Phase Locked Loop (PLL) blocks. These blocks are located at the ends of the on-chip NVCM/Flash block. The PLLs have multiply, divide, and phase shifting capabilities that are used to manage the frequency and phase relationships of the clocks.

MachXO3L/LF devices provide commonly used hardened functions such as SPI controller, I<sup>2</sup>C controller and timer/ counter.

MachXO3LF devices also provide User Flash Memory (UFM). These hardened functions and the UFM interface to the core logic and routing through a WISHBONE interface. The UFM can also be accessed through the SPI, I<sup>2</sup>C and JTAG ports.

Every device in the family has a JTAG port that supports programming and configuration of the device as well as access to the user logic. The MachXO3L/LF devices are available for operation from 3.3 V, 2.5 V and 1.2 V power sup-plies, providing easy integration into the overall system.



### Modes of Operation

Each slice has up to four potential modes of operation: Logic, Ripple, RAM and ROM.

#### Logic Mode

In this mode, the LUTs in each slice are configured as 4-input combinatorial lookup tables. A LUT4 can have 16 possible input combinations. Any four input logic functions can be generated by programming this lookup table. Since there are two LUT4s per slice, a LUT5 can be constructed within one slice. Larger look-up tables such as LUT6, LUT7 and LUT8 can be constructed by concatenating other slices. Note LUT8 requires more than four slices.

#### **Ripple Mode**

Ripple mode supports the efficient implementation of small arithmetic functions. In Ripple mode, the following functions can be implemented by each slice:

- Addition 2-bit
- Subtraction 2-bit
- Add/subtract 2-bit using dynamic control
- Up counter 2-bit
- Down counter 2-bit
- Up/down counter with asynchronous clear
- Up/down counter with preload (sync)
- Ripple mode multiplier building block
- Multiplier support
- Comparator functions of A and B inputs
  - A greater-than-or-equal-to B
  - A not-equal-to B
  - A less-than-or-equal-to B

Ripple mode includes an optional configuration that performs arithmetic using fast carry chain methods. In this configuration (also referred to as CCU2 mode) two additional signals, Carry Generate and Carry Propagate, are generated on a per-slice basis to allow fast arithmetic functions to be constructed by concatenating slices.

#### **RAM Mode**

In this mode, a 16x4-bit distributed single port RAM (SPR) can be constructed by using each LUT block in Slice 0 and Slice 1 as a 16x1-bit memory. Slice 2 is used to provide memory address and control signals.

MachXO3L/LF devices support distributed memory initialization.

The Lattice design tools support the creation of a variety of different size memories. Where appropriate, the software will construct these using distributed memory primitives that represent the capabilities of the PFU. Table 2-3 shows the number of slices required to implement different distributed RAM primitives. For more information about using RAM in MachXO3L/LF devices, please see TN1290, Memory Usage Guide for MachXO3 Devices.

#### Table 2-3. Number of Slices Required For Implementing Distributed RAM

	SPR 16x4	PDPR 16x4				
Number of slices	3	3				
Note: SPB = Single Port BAM. PDPB = Pseudo Dual Port BAM						

ote: SPR = Single Port RAM, PDPR = Pseudo Dual



Port Name	Description	Active State
CLK	Clock	Rising Clock Edge
CE	Clock Enable	Active High
OCE <sup>1</sup>	Output Clock Enable	Active High
RST	Reset	Active High
BE <sup>1</sup>	Byte Enable	Active High
WE	Write Enable	Active High
AD	Address Bus	—
DI	Data In	_
DO	Data Out	_
CS	Chip Select	Active High
AFF	FIFO RAM Almost Full Flag	_
FF	FIFO RAM Full Flag	_
AEF	FIFO RAM Almost Empty Flag	_
EF	FIFO RAM Empty Flag	_
RPRST	FIFO RAM Read Pointer Reset	_

#### Table 2-6. EBR Signal Descriptions

1. Optional signals.

2. For dual port EBR primitives a trailing 'A' or 'B' in the signal name specifies the EBR port A or port B respectively.

3. For FIFO RAM mode primitive, a trailing 'R' or 'W' in the signal name specifies the FIFO read port or write port respectively.

4. For FIFO RAM mode primitive FULLI has the same function as CSW(2) and EMPTYI has the same function as CSR(2).

In FIFO mode, CLKW is the write port clock, CSW is the write port chip select, CLKR is the read port clock, CSR is the read port clock, CSR is the read port clock.

The EBR memory supports three forms of write behavior for single or dual port operation:

- 1. **Normal** Data on the output appears only during the read cycle. During a write cycle, the data (at the current address) does not appear on the output. This mode is supported for all data widths.
- 2. Write Through A copy of the input data appears at the output of the same port. This mode is supported for all data widths.
- 3. Read-Before-Write When new data is being written, the old contents of the address appears at the output.

#### **FIFO Configuration**

The FIFO has a write port with data-in, CEW, WE and CLKW signals. There is a separate read port with data-out, RCE, RE and CLKR signals. The FIFO internally generates Almost Full, Full, Almost Empty and Empty Flags. The Full and Almost Full flags are registered with CLKW. The Empty and Almost Empty flags are registered with CLKR. Table 2-7 shows the range of programming values for these flags.

#### Table 2-7. Programmable FIFO Flag Ranges

Flag Name	Programming Range
Full (FF)	1 to max (up to 2 <sup>N</sup> -1)
Almost Full (AF)	1 to Full-1
Almost Empty (AE)	1 to Full-1
Empty (EF)	0

N = Address bit width.

The FIFO state machine supports two types of reset signals: RST and RPRST. The RST signal is a global reset that clears the contents of the FIFO by resetting the read/write pointer and puts the FIFO flags in their initial reset



#### Figure 2-13. Input Gearbox



More information on the input gearbox is available in TN1281, Implementing High-Speed Interfaces with MachXO3 Devices.



#### Figure 2-14. Output Gearbox



More information on the output gearbox is available in TN1281, Implementing High-Speed Interfaces with MachXO3 Devices.



Table 2-11 shows the I/O standards (together with their supply and reference voltages) supported by the MachXO3L/LF devices. For further information on utilizing the sysIO buffer to support a variety of standards please see TN1280, MachXO3 sysIO Usage Guide.

#### Table 2-11. Supported Input Standards

		VCCIO (Typ.)					
Input Standard	3.3 V	2.5 V	1.8 V	1.5 V	1.2 V		
Single-Ended Interfaces							
LVTTL	Yes						
LVCMOS33	Yes						
LVCMOS25		Yes					
LVCMOS18			Yes				
LVCMOS15				Yes			
LVCMOS12					Yes		
PCI	Yes						
Differential Interfaces		•					
LVDS	Yes	Yes					
BLVDS, MLVDS, LVPECL, RSDS	Yes	Yes					
MIPI <sup>1</sup>	Yes	Yes					
LVTTLD	Yes						
LVCMOS33D	Yes						
LVCMOS25D		Yes					
LVCMOS18D			Yes				

1. These interfaces can be emulated with external resistors in all devices.



# Figure 2-15. MachXO3L/LF-1300 in 256 Ball Packages, MachXO3L/LF-2100, MachXO3L/LF-4300, MachXO3L/LF-6900 and MachXO3L/LF-9400 Banks



Figure 2-16. MachXO3L/LF-640 and MachXO3L/LF-1300 Banks





# **Configuration and Testing**

This section describes the configuration and testing features of the MachXO3L/LF family.

### IEEE 1149.1-Compliant Boundary Scan Testability

All MachXO3L/LF devices have boundary scan cells that are accessed through an IEEE 1149.1 compliant test access port (TAP). This allows functional testing of the circuit board, on which the device is mounted, through a serial scan path that can access all critical logic nodes. Internal registers are linked internally, allowing test data to be shifted in and loaded directly onto test nodes, or test data to be captured and shifted out for verification. The test access port consists of dedicated I/Os: TDI, TDO, TCK and TMS. The test access port shares its power supply with  $V_{CCIO}$  Bank 0 and can operate with LVCMOS3.3, 2.5, 1.8, 1.5, and 1.2 standards.

For more details on boundary scan test, see AN8066, Boundary Scan Testability with Lattice sysIO Capability and TN1087, Minimizing System Interruption During Configuration Using TransFR Technology.

### **Device Configuration**

All MachXO3L/LF devices contain two ports that can be used for device configuration. The Test Access Port (TAP), which supports bit-wide configuration and the sysCONFIG port which supports serial configuration through I<sup>2</sup>C or SPI. The TAP supports both the IEEE Standard 1149.1 Boundary Scan specification and the IEEE Standard 1532 In-System Configuration specification. There are various ways to configure a MachXO3L/LF device:

- 1. Internal NVCM/Flash Download
- 2. JTAG
- 3. Standard Serial Peripheral Interface (Master SPI mode) interface to boot PROM memory
- 4. System microprocessor to drive a serial slave SPI port (SSPI mode)
- 5. Standard I<sup>2</sup>C Interface to system microprocessor

Upon power-up, the configuration SRAM is ready to be configured using the selected sysCONFIG port. Once a configuration port is selected, it will remain active throughout that configuration cycle. The IEEE 1149.1 port can be activated any time after power-up by sending the appropriate command through the TAP port. Optionally the device can run a CRC check upon entering the user mode. This will ensure that the device was configured correctly.

The sysCONFIG port has 10 dual-function pins which can be used as general purpose I/Os if they are not required for configuration. See TN1279, MachXO3 Programming and Configuration Usage Guide for more information about using the dual-use pins as general purpose I/Os.

Lattice design software uses proprietary compression technology to compress bit-streams for use in MachXO3L/ LF devices. Use of this technology allows Lattice to provide a lower cost solution. In the unlikely event that this technology is unable to compress bitstreams to fit into the amount of on-chip NVCM/Flash, there are a variety of techniques that can be utilized to allow the bitstream to fit in the on-chip NVCM/Flash. For more details, refer to TN1279, MachXO3 Programming and Configuration Usage Guide.

The Test Access Port (TAP) has five dual purpose pins (TDI, TDO, TMS, TCK and JTAGENB). These pins are dual function pins - TDI, TDO, TMS and TCK can be used as general purpose I/O if desired. For more details, refer to TN1279, MachXO3 Programming and Configuration Usage Guide.

#### TransFR (Transparent Field Reconfiguration)

TransFR is a unique Lattice technology that allows users to update their logic in the field without interrupting system operation using a simple push-button solution. For more details refer to TN1087, Minimizing System Interruption During Configuration Using TransFR Technology for details.



#### Security and One-Time Programmable Mode (OTP)

For applications where security is important, the lack of an external bitstream provides a solution that is inherently more secure than SRAM-based FPGAs. This is further enhanced by device locking. MachXO3L/LF devices contain security bits that, when set, prevent the readback of the SRAM configuration and NVCM/Flash spaces. The device can be in one of two modes:

- 1. Unlocked Readback of the SRAM configuration and NVCM/Flash spaces is allowed.
- 2. Permanently Locked The device is permanently locked.

Once set, the only way to clear the security bits is to erase the device. To further complement the security of the device, a One Time Programmable (OTP) mode is available. Once the device is set in this mode it is not possible to erase or re-program the NVCM/Flash and SRAM OTP portions of the device. For more details, refer to TN1279, MachXO3 Programming and Configuration Usage Guide.

#### Password

The MachXO3LF supports a password-based security access feature also known as Flash Protect Key. Optionally, the MachXO3L device can be ordered with a custom specification (c-spec) to support this feature. The Flash Protect Key feature provides a method of controlling access to the Configuration and Programming modes of the device. When enabled, the Configuration and Programming edit mode operations (including Write, Verify and Erase operations) are allowed only when coupled with a Flash Protect Key which matches that expected by the device. Without a valid Flash Protect Key, the user can perform only rudimentary non-configuration operations such as Read Device ID. For more details, refer to TN1313, Using Password Security with MachXO3 Devices.

#### **Dual Boot**

MachXO3L/LF devices can optionally boot from two patterns, a primary bitstream and a golden bitstream. If the primary bitstream is found to be corrupt while being downloaded into the SRAM, the device shall then automatically re-boot from the golden bitstream. Note that the primary bitstream must reside in the external SPI Flash. The golden image MUST reside in an on-chip NVCM/Flash. For more details, refer to TN1279, MachXO3 Programming and Configuration Usage Guide.

#### Soft Error Detection

The SED feature is a CRC check of the SRAM cells after the device is configured. This check ensures that the SRAM cells were configured successfully. This feature is enabled by a configuration bit option. The Soft Error Detection can also be initiated in user mode via an input to the fabric. The clock for the Soft Error Detection circuit is generated using a dedicated divider. The undivided clock from the on-chip oscillator is the input to this divider. For low power applications users can switch off the Soft Error Detection circuit. For more details, refer to TN1292, MachXO3 Soft Error Detection Usage Guide.

#### Soft Error Correction

The MachXO3LF device supports Soft Error Correction (SEC). Optionally, the MachXO3L device can be ordered with a custom specification (c-spec) to support this feature. When BACKGROUND\_RECONFIG is enabled using the Lattice Diamond Software in a design, asserting the PROGRAMN pin or issuing the REFRESH sysConfig command refreshes the SRAM array from configuration memory. Only the detected error bit is corrected. No other SRAM cells are changed, allowing the user design to function uninterrupted.

During the project design phase, if the overall system cannot guarantee containment of the error or its subsequent effects on downstream data or control paths, Lattice recommends using SED only. The MachXO3 can be then be soft-reset by asserting PROGRAMN or issuing the Refresh command over a sysConfig port in response to SED. Soft-reset additionally erases the SRAM array prior to the SRAM refresh, and asserts internal Reset circuitry to guarantee a known state. For more details, refer to TN1292, MachXO3 Soft Error Detection (SED)/Correction (SEC) Usage Guide.



## TraceID

Each MachXO3L/LF device contains a unique (per device), TraceID that can be used for tracking purposes or for IP security applications. The TraceID is 64 bits long. Eight out of 64 bits are user-programmable, the remaining 56 bits are factory-programmed. The TraceID is accessible through the EFB WISHBONE interface and can also be accessed through the SPI, I<sup>2</sup>C, or JTAG interfaces.

### **Density Shifting**

The MachXO3L/LF family has been designed to enable density migration within the same package. Furthermore, the architecture ensures a high success rate when performing design migration from lower density devices to higher density devices. In many cases, it is also possible to shift a lower utilization design targeted for a high-density device to a lower density device. However, the exact details of the final resource utilization will impact the likely success in each case. When migrating from lower to higher density or higher to lower density, ensure to review all the power supplies and NC pins of the chosen devices. For more details refer to the MachXO3 migration files.



# sysIO Single-Ended DC Electrical Characteristics<sup>1, 2</sup>

Input/Output	V	IL	V	IH	V <sub>OL</sub> Max.	V <sub>OH</sub> Min.	I <sub>OL</sub> Max.⁴	l <sub>OH</sub> Max.⁴
Standard	Min. (V) <sup>3</sup>	Max. (V)	Min. (V)	Max. (V)	(V)	(V)	(mA)	(mA)
							4	-4
					0.4	V <sub>CCIO</sub> - 0.4	8	-8
LVCMOS 3.3 LVTTL	-0.3	0.8	2.0	3.6	0.4	CCIO - 0.4	12	-12
							16	-16
					0.2	V <sub>CCIO</sub> - 0.2	0.1	-0.1
							4	-4
					0.4	V <sub>CCIO</sub> - 0.4	8	-8
LVCMOS 2.5	-0.3	0.7	1.7	3.6	0.4	VCCIO - 0.4	12	-12
							16	-16
					0.2	V <sub>CCIO</sub> - 0.2	0.1	-0.1
	-0.3						4	-4
LVCMOS 1.8		0.251/	0.651/	3.6 0.4 V <sub>CCIO</sub> - 0.4	8	-8		
	-0.3	0.35V <sub>CCIO</sub>	0.65V <sub>CCIO</sub>	3.0			12	-12
					0.2	V <sub>CCIO</sub> - 0.2	0.1	-0.1
					0.4	V <sub>CCIO</sub> - 0.4	4	-4
LVCMOS 1.5	-0.3	$0.35V_{CCIO}$	$0.65V_{CCIO}$	3.6	0.4		8	-8
					0.2	V <sub>CCIO</sub> - 0.2	0.1	-0.1
	-0.3	0.35V <sub>CCIO</sub>	0.65V <sub>CCIO</sub>		0.4	V 0.4	4	-2
VCMOS 1.2				3.6	0.4	V <sub>CCIO</sub> - 0.4	8	-6
					0.2	V <sub>CCIO</sub> - 0.2	0.1	-0.1
LVCMOS25R33	-0.3	VREF-0.1	VREF+0.1	3.6	NA	NA	NA	NA
LVCMOS18R33	-0.3	VREF-0.1	VREF+0.1	3.6	NA	NA	NA	NA
LVCMOS18R25	-0.3	VREF-0.1	VREF+0.1	3.6	NA	NA	NA	NA
LVCMOS15R33	-0.3	VREF-0.1	VREF+0.1	3.6	NA	NA	NA	NA
LVCMOS15R25	-0.3	VREF-0.1	VREF+0.1	3.6	NA	NA	NA	NA
LVCMOS12R33	-0.3	VREF-0.1	VREF+0.1	3.6	0.40	NA Open Drain	24, 16, 12, 8, 4	NA Open Drain
LVCMOS12R25	-0.3	VREF-0.1	VREF+0.1	3.6	0.40	NA Open Drain	16, 12, 8, 4	NA Open Drain
LVCMOS10R33	-0.3	VREF-0.1	VREF+0.1	3.6	0.40	NA Open Drain	24, 16, 12, 8, 4	NA Open Drain
LVCMOS10R25	-0.3	VREF-0.1	VREF+0.1	3.6	0.40	NA Open Drain	16, 12, 8, 4	NA Open Drain

 MachXO3L/LF devices allow LVCMOS inputs to be placed in I/O banks where V<sub>CCIO</sub> is different from what is specified in the applicable JEDEC specification. This is referred to as a ratioed input buffer. In a majority of cases this operation follows or exceeds the applicable JEDEC specification. The cases where MachXO3L/LF devices do not meet the relevant JEDEC specification are documented in the table below.

2. MachXO3L/LF devices allow for LVCMOS referenced I/Os which follow applicable JEDEC specifications. For more details about mixed mode operation please refer to please refer to TN1280, MachXO3 sysIO Usage Guide.

3. The dual function I<sup>2</sup>C pins SCL and SDA are limited to a  $V_{IL}$  min of -0.25 V or to -0.3 V with a duration of <10 ns.

4. For electromigration, the average DC current sourced or sinked by I/O pads between two consecutive VCCIO or GND pad connections, or between the last VCCIO or GND in an I/O bank and the end of an I/O bank, as shown in the Logic Signal Connections table (also shown as I/O grouping) shall not exceed a maximum of n \* 8 mA. "n" is the number of I/O pads between the two consecutive bank VCCIO or GND connections or between the last VCCIO and GND in a bank and the end of a bank. IO Grouping can be found in the Data Sheet Pin Tables, which can also be generated from the Lattice Diamond software.



# sysIO Differential Electrical Characteristics

The LVDS differential output buffers are available on the top side of the MachXO3L/LF PLD family.

### LVDS

Parameter Symbol	Parameter Description	Test Conditions	Min.	Тур.	Max.	Units
V V	Input Voltage	V <sub>CCIO</sub> = 3.3 V	0	_	2.605	V
Symbol           / <sub>INP</sub> V <sub>INM</sub> I           / <sub>THD</sub> I           / <sub>CM</sub> I           / <sub>CM</sub> I           / <sub>OH</sub> I           / <sub>OL</sub> I           / <sub>OL</sub> I           V <sub>OD</sub> I           V <sub>OS</sub> I		$V_{CCIO} = 2.5 V$	0		2.05	V
V <sub>THD</sub>	Differential Input Threshold		±100			mV
M	Innut Common Made Voltage	$V_{CCIO} = 3.3 V$	0.05	_	2.6	V
V <sub>CM</sub>	Input Common Mode Voltage	$V_{CCIO} = 2.5 V$	0.05		2.0	V
I <sub>IN</sub>	Input current	Power on	_	_	±10	μA
V <sub>OH</sub>	Output high voltage for V <sub>OP</sub> or V <sub>OM</sub>	R <sub>T</sub> = 100 Ohm	_	1.375	—	V
V <sub>OL</sub>	Output low voltage for $V_{OP}$ or $V_{OM}$	R <sub>T</sub> = 100 Ohm	0.90	1.025	—	V
V <sub>OD</sub>	Output voltage differential	(V <sub>OP</sub> - V <sub>OM</sub> ), R <sub>T</sub> = 100 Ohm	250	350	450	mV
ΔV <sub>OD</sub>	Change in V <sub>OD</sub> between high and low		_	_	50	mV
V <sub>OS</sub>	Output voltage offset	$(V_{OP} - V_{OM})/2, R_{T} = 100 \text{ Ohm}$	1.125	1.20	1.395	V
ΔV <sub>OS</sub>	Change in V <sub>OS</sub> between H and L		_	_	50	mV
IOSD	Output short circuit current	V <sub>OD</sub> = 0 V driver outputs shorted	_	_	24	mA

### **Over Recommended Operating Conditions**



### LVDS Emulation

MachXO3L/LF devices can support LVDS outputs via emulation (LVDS25E). The output is emulated using complementary LVCMOS outputs in conjunction with resistors across the driver outputs on all devices. The scheme shown in Figure 3-1 is one possible solution for LVDS standard implementation. Resistor values in Figure 3-1 are industry standard values for 1% resistors.





Note: All resistors are ±1%.

#### Table 3-1. LVDS25E DC Conditions

#### **Over Recommended Operating Conditions**

Parameter	Description	Тур.	Units					
Z <sub>OUT</sub>	Output impedance	20	Ohms					
R <sub>S</sub>	Driver series resistor	158	Ohms					
R <sub>P</sub>	Driver parallel resistor	140	Ohms					
R <sub>T</sub>	Receiver termination	100	Ohms					
V <sub>OH</sub>	Output high voltage	1.43	V					
V <sub>OL</sub>	Output low voltage	1.07	V					
V <sub>OD</sub>	Output differential voltage	0.35	V					
V <sub>CM</sub>	Output common mode voltage	1.25	V					
Z <sub>BACK</sub>	Back impedance	100.5	Ohms					
I <sub>DC</sub>	DC output current	6.03	mA					



### DC and Switching Characteristics MachXO3 Family Data Sheet

			-	-6	-	5	
Parameter	Description	Device	Min.	Max.	Min.	Max.	Units
	DRX4 Outputs with Clock and Data Centere X.ECLK.Centered <sup>8, 9</sup>	d at Pin Using PCLK Pin f	or Clock	Input –			
t <sub>DVB</sub>	Output Data Valid Before CLK Output		0.455	—	0.570		ns
t <sub>DVA</sub>	Output Data Valid After CLK Output		0.455	—	0.570	—	ns
f <sub>DATA</sub>	DDRX4 Serial Output Data Speed	MachXO3L/LF devices,	—	800		630	Mbps
f <sub>DDRX4</sub>	DDRX4 ECLK Frequency (minimum limited by PLL)	top side only	_	400	_	315	MHz
f <sub>SCLK</sub>	SCLK Frequency	_	_	100	—	79	MHz
7:1 LVDS 0	outputs – GDDR71_TX.ECLK.7:1 <sup>8,9</sup>		•	•			
t <sub>DIB</sub>	Output Data Invalid Before CLK Output		—	0.160		0.180	ns
t <sub>DIA</sub>	Output Data Invalid After CLK Output		—	0.160	—	0.180	ns
f <sub>DATA</sub>	DDR71 Serial Output Data Speed	MachXO3L/LF devices,	—	756	—	630	Mbps
f <sub>DDR71</sub>	DDR71 ECLK Frequency	top side only	—	378		315	MHz
f <sub>CLKOUT</sub>	7:1 Output Clock Frequency (SCLK) (mini- mum limited by PLL)	-	_	108	_	90	MHz
	Outputs with Clock and Data Centered at F X.ECLK.Centered <sup>10, 11, 12</sup>	in Using PCLK Pin for Clo	ck Input	-			
t <sub>DVB</sub>	Output Data Valid Before CLK Output		0.200	—	0.200		UI
t <sub>DVA</sub>	Output Data Valid After CLK Output		0.200	—	0.200		UI
f <sub>DATA</sub> <sup>14</sup>	MIPI D-PHY Output Data Speed	All MachXO3L/LF	—	900		900	Mbps
f <sub>DDRX4</sub> <sup>14</sup>	MIPI D-PHY ECLK Frequency (minimum limited by PLL)	devices, top side only	_	450	—	450	MHz
f <sub>SCLK</sub> <sup>14</sup>	SCLK Frequency	1	—	112.5	—	112.5	MHz

1. Exact performance may vary with device and design implementation. Commercial timing numbers are shown at 85 °C and 1.14 V. Other operating conditions, including industrial, can be extracted from the Diamond software.

2. General I/O timing numbers based on LVCMOS 2.5, 8 mA, 0pf load, fast slew rate.

3. Generic DDR timing numbers based on LVDS I/O (for input, output, and clock ports).

4. 7:1 LVDS (GDDR71) uses the LVDS I/O standard (for input, output, and clock ports).

5. For Generic DDRX1 mode  $t_{SU} = t_{HO} = (t_{DVE} - t_{DVA} - 0.03 \text{ ns})/2$ .

6. The t<sub>SU DEL</sub> and t<sub>H DEL</sub> values use the SCLK\_ZERHOLD default step size. Each step is 105 ps (-6), 113 ps (-5), 120 ps (-4).

7. This number for general purpose usage. Duty cycle tolerance is +/-10%.

8. Duty cycle is  $\pm -5\%$  for system usage.

9. Performance is calculated with 0.225 UI.

10. Performance is calculated with 0.20 UI.

11. Performance for Industrial devices are only supported with VCC between 1.16 V to 1.24 V.

12. Performance for Industrial devices and -5 devices are not modeled in the Diamond design tool.

13. The above timing numbers are generated using the Diamond design tool. Exact performance may vary with the device selected.

14. Above 800 Mbps is only supported with WLCSP and csfBGA packages

15. Between 800 Mbps to 900 Mbps:

a. VIDTH exceeds the MIPI D-PHY Input DC Conditions Table 3-4 and can be calculated with the equation tSU or tH = -0.0005\*VIDTH + 0.3284

b. Example calculations

i. tSU and tHO = 0.28 with VIDTH = 100 mV

ii. tSU and tHO = 0.25 with VIDTH = 170 mV

iii. tSU and tHO = 0.20 with VIDTH = 270 mV



# NVCM/Flash Download Time<sup>1, 2</sup>

Symbol	Parameter	Device	Тур.	Units
t <sub>REFRESH</sub>	POR to Device I/O Active	LCMXO3L/LF-640	1.9	ms
		LCMXO3L/LF-1300	1.9	ms
		LCMXO3L/LF-1300 256-Ball Package	1.4	ms
		LCMXO3L/LF-2100	1.4	ms
		LCMXO3L/LF-2100 324-Ball Package	2.4	ms
		LCMXO3L/LF-4300	2.4	ms
		LCMXO3L/LF-4300 400-Ball Package	3.8	ms
		LCMXO3L/LF-6900	3.8	ms
		LCMXO3L/LF-9400C	5.2	ms

1. Assumes sysMEM EBR initialized to an all zero pattern if they are used.

2. The NVCM/Flash download time is measured starting from the maximum voltage of POR trip point.



Part Number	LUTs	Supply Voltage	Speed	Package	Leads	Temp.
LCMXO3L-2100E-6MG324I	2100	1.2 V	6	Halogen-Free csfBGA	324	IND
LCMXO3L-2100C-5BG256C	2100	2.5 V / 3.3 V	5	Halogen-Free caBGA	256	СОМ
LCMXO3L-2100C-6BG256C	2100	2.5 V / 3.3 V	6	Halogen-Free caBGA	256	COM
LCMXO3L-2100C-5BG256I	2100	2.5 V / 3.3 V	5	Halogen-Free caBGA	256	IND
LCMXO3L-2100C-6BG256I	2100	2.5 V / 3.3 V	6	Halogen-Free caBGA	256	IND
LCMXO3L-2100C-5BG324C	2100	2.5 V / 3.3 V	5	Halogen-Free caBGA	324	COM
LCMXO3L-2100C-6BG324C	2100	2.5 V / 3.3 V	6	Halogen-Free caBGA	324	COM
LCMXO3L-2100C-5BG324I	2100	2.5 V / 3.3 V	5	Halogen-Free caBGA	324	IND
LCMXO3L-2100C-6BG324I	2100	2.5 V / 3.3 V	6	Halogen-Free caBGA	324	IND
Part Number	LUTs	Supply Voltage	Speed	Package	Leads	Temp.
LCMXO3L-4300E-5UWG81CTR	4300	1.2 V	5	Halogen-Free WLCSP	81	COM
LCMXO3L-4300E-5UWG81CTR50	4300	1.2 V	5	Halogen-Free WLCSP	81	COM
LCMXO3L-4300E-5UWG81CTR1K	4300	1.2 V	5	Halogen-Free WLCSP	81	COM
LCMXO3L-4300E-5UWG81ITR	4300	1.2 V	5	Halogen-Free WLCSP	81	IND
LCMXO3L-4300E-5UWG81ITR50	4300	1.2 V	5	Halogen-Free WLCSP	81	IND
LCMXO3L-4300E-5UWG81ITR1K	4300	1.2 V	5	Halogen-Free WLCSP	81	IND
LCMXO3L-4300E-5MG121C	4300	1.2 V	5	Halogen-Free csfBGA	121	COM
LCMXO3L-4300E-6MG121C	4300	1.2 V	6	Halogen-Free csfBGA	121	COM
LCMXO3L-4300E-5MG121I	4300	1.2 V	5	Halogen-Free csfBGA	121	IND
LCMXO3L-4300E-6MG121I	4300	1.2 V	6	Halogen-Free csfBGA	121	IND
LCMXO3L-4300E-5MG256C	4300	1.2 V	5	Halogen-Free csfBGA	256	COM
LCMXO3L-4300E-6MG256C	4300	1.2 V	6	Halogen-Free csfBGA	256	COM
LCMXO3L-4300E-5MG256I	4300	1.2 V	5	Halogen-Free csfBGA	256	IND
LCMXO3L-4300E-6MG256I	4300	1.2 V	6	Halogen-Free csfBGA	256	IND
LCMXO3L-4300E-5MG324C	4300	1.2 V	5	Halogen-Free csfBGA	324	COM
LCMXO3L-4300E-6MG324C	4300	1.2 V	6	Halogen-Free csfBGA	324	COM
LCMXO3L-4300E-5MG324I	4300	1.2 V	5	Halogen-Free csfBGA	324	IND
LCMXO3L-4300E-6MG324I	4300	1.2 V	6	Halogen-Free csfBGA	324	IND
LCMXO3L-4300C-5BG256C	4300	2.5 V / 3.3 V	5	Halogen-Free caBGA	256	COM
LCMXO3L-4300C-6BG256C	4300	2.5 V / 3.3 V	6	Halogen-Free caBGA	256	COM
LCMXO3L-4300C-5BG256I	4300	2.5 V / 3.3 V	5	Halogen-Free caBGA	256	IND
LCMXO3L-4300C-6BG256I	4300	2.5 V / 3.3 V	6	Halogen-Free caBGA	256	IND
LCMXO3L-4300C-5BG324C	4300	2.5 V / 3.3 V	5	Halogen-Free caBGA	324	COM
LCMXO3L-4300C-6BG324C	4300	2.5 V / 3.3 V	6	Halogen-Free caBGA	324	COM
LCMXO3L-4300C-5BG324I	4300	2.5 V / 3.3 V	5	Halogen-Free caBGA	324	IND
LCMXO3L-4300C-6BG324I	4300	2.5 V / 3.3 V	6	Halogen-Free caBGA	324	IND
LCMXO3L-4300C-5BG400C	4300	2.5 V / 3.3 V	5	Halogen-Free caBGA	400	СОМ
LCMXO3L-4300C-6BG400C	4300	2.5 V / 3.3 V	6	Halogen-Free caBGA	400	СОМ
LCMXO3L-4300C-5BG400I	4300	2.5 V / 3.3 V	5	Halogen-Free caBGA	400	IND
LCMXO3L-4300C-6BG400I	4300	2.5 V / 3.3 V	6	Halogen-Free caBGA	400	IND



# MachXO3 Family Data Sheet Revision History

#### February 2017

Advance Data Sheet DS1047

Date	Version	Section	Change Summary
February 2017	1.8	Architecture	Updated Supported Standards section. Corrected "MDVS" to "MLDVS" in Table 2-11, Supported Input Standards.
		DC and Switching Characteristics	Updated ESD Performance section. Added reference to the MachXO2 Product Family Qualification Summary document.
			Updated Static Supply Current – C/E Devices section. Added footnote 7.
			Updated MachXO3L/LF External Switching Characteristics – C/E Devices section. — Populated values for MachXO3L/LF-9400. — Under 7:1 LVDS Outputs – GDDR71_TX.ECLK.7:1, corrected "t <sub>DVB</sub> " to "t <sub>DIB</sub> " and "t <sub>DVA</sub> " to "t <sub>DIA</sub> " and revised their descriptions. — Added Figure 3-6, Receiver GDDR71_RX Waveforms and Figure 3-7, Transmitter GDDR71_TX Waveforms.
		Pinout Information	Updated the Pin Information Summary section. Added MachXO3L/LF- 9600C packages.
May 2016	1.7	DC and Switching Characteristics	Updated Absolute Maximum Ratings section. Modified I/O Tri-state Volt- age Applied and Dedicated Input Voltage Applied footnotes.
			Updated sysIO Recommended Operating Conditions section. — Added standards. — Added V <sub>REF</sub> (V) — Added footnote 4.
			Updated sysIO Single-Ended DC Electrical Characteristics section. Added I/O standards.
		Ordering Information	Updated MachXO3L Ultra Low Power Commercial and Industrial Grade Devices, Halogen Free (RoHS) Packaging section. Added LCMXO3L-9400C part numbers.
			Updated MachXO3LF Ultra Low Power Commercial and Industrial Grade Devices, Halogen Free (RoHS) Packaging section. Added LCMXO3L-9400C part numbers.

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Date	Version	Section	Change Summary
September 2015	1.5	DC and Switching Characteristics	Updated the MIPI D-PHY Emulation section. Revised Table 3-5, MIPI D- PHY Output DC Conditions. — Revised RL Typ. value. — Revised RH description and values.
			Updated the Maximum sysIO Buffer Performance section. Revised MIPI Max. Speed value.
			Updated the MachXO3L/LF External Switching Characteristics – C/E Devices section. Added footnotes 14 and 15.
August 2015	1.4	Architecture	Updated the Device Configuration section. Added JTAGENB to TAP dual purpose pins.
		Ordering Information	Updated the top side markings section to indicate the use of LMXO3LF for the LCMXO3LF device.
March 2015	1.3	All	General update. Added MachXO3LF devices.
October 2014	1.2	Introduction	Updated Table 1-1, MachXO3L Family Selection Guide. Revised XO3L- 2100 and XO3L-4300 IO for 324-ball csfBGA package.
		Architecture	Updated the Dual Boot section. Corrected information on where the pri- mary bitstream and the golden image must reside.
		Pinout Information	Updated the Pin Information Summary section.
			Changed General Purpose IO Bank 5 values for MachXO3L-2100 and MachXO3L-4300 CSFBGA 324 package.
			Changed Number 7:1 or 8:1 Gearboxes for MachXO3L-640 and MachXO3L-1300.
			Removed DQS Groups (Bank 1) section.
			Changed VCCIO Pins Bank 1 values for MachXO3L-1300, MachXO3L- 2100, MachXO3L-4300 and MachXO3L-6900 CSFBGA 256 package.
			Changed GND values for MachXO3L-1300, MachXO3L-2100, MachXO3L-4300 and MachXO3L-6900 CSFBGA 256 package.
			Changed NC values for MachXO3L-2100 and MachXO3L-4300 CSF- BGA 324 package.
		DC and Switching Characteristics	Updated the BLVDS section. Changed output impedance nominal values in Table 3-2, BLVDS DC Condition.
			Updated the LVPECL section. Changed output impedance nominal value in Table 3-3, LVPECL DC Condition.
			Updated the sysCONFIG Port Timing Specifications section. Updated INITN low time values.
July 2014	1.1	DC and Switching Characteristics	Updated the Static Supply Current – C/E Devices section. Added devices.
			Updated the Programming and Erase Supply Current – C/E Device section. Added devices.
			Updated the sysIO Single-Ended DC Electrical Characteristics section. Revised footnote 4.
			Added the NVCM Download Time section.
			Updated the Typical Building Block Function Performance – C/E Devices section. Added information to footnote.
		Pinout Information	Updated the Pin Information Summary section.
		Ordering Information	Updated the MachXO3L Part Number Description section. Added pack- ages.
			Updated the Ordering Information section. General update.





Date	Version	Section	Change Summary
June 2014	1.0	—	Product name/trademark adjustment.
		Introduction	Updated Features section.
			Updated Table 1-1, MachXO3L Family Selection Guide. Changed fcCSP packages to csfBGA. Adjusted 121-ball csfBGA arrow.
			Introduction section general update.
		Architecture	General update.
		DC and Switching Characteristics	Updated sysIO Recommended Operating Conditions section. Removed V <sub>REF</sub> (V) column. Added standards.
			Updated Maximum sysIO Buffer Performance section. Added MIPI I/O standard.
			Updated MIPI D-PHY Emulation section. Changed Low Speed to Low Power. Updated Table 3-4, MIPI DC Conditions.
			Updated Table 3-5, MIPI D-PHY Output DC Conditions.
			Updated Maximum sysIO Buffer Performance section.
			Updated MachXO3L External Switching Characteristics – C/E Device section.
May 2014	00.3	Introduction	Updated Features section.
			Updated Table 1-1, MachXO3L Family Selection Guide. Moved 121-ball fcCSP arrow.
			General update of Introduction section.
		Architecture	General update.
		Pinout Information	Updated Pin Information Summary section. Updated or added data on WLCSP49, WLCSP81, CABGA324, and CABGA400 for specific devices.
		Ordering Information	Updated MachXO3L Part Number Description section. Updated or added data on WLCSP49, WLCSP81, CABGA324, and CABGA400 for specific devices.
			Updated Ultra Low Power Commercial and Industrial Grade Devices, Halogen Free (RoHS) Packaging section. Added part numbers.
February 2014	00.2	DC and Switching Characteristics	Updated MachXO3L External Switching Characteristics – C/E Devices table. Removed LPDDR and DDR2 parameters.
	00.1		Initial release.